WHAT IS CLAIMED IS:

1. An electronic device comprising a nonvolatile memory,

wherein the nonvolatile memory comprises a memory element, and

wherein the memory element comprises a first thin film transistor comprising a floating gate and a second thin film transistor.

2. An electronic device comprising a nonvolatile memory,

wherein the nonvolatile memory comprises a memory element,

wherein the memory element comprises a first thin film transistor comprising a floating gate and a second thin film transistor, and

wherein a source electrode and a drain electrode of the memory element comprise the same material as that of a gate electrode of the first thin film transistor.

3. An electronic device comprising:

a nonvolatile memory; and

a semiconductor display device comprising a pixel region comprising a plurality of pixel thin film transistors,

wherein the nonvolatile memory comprises a memory element,

wherein the memory element comprises a first thin film transistor comprising a floating gate and a second thin film transistor, and

wherein gate electrodes of the plurality of pixel thin film transistors, the floating gate, and a gate electrode of the second thin film transistor comprise the same material.

4. An electronic device comprising:

a nonvolatile memory; and

a semiconductor display device comprising a pixel region comprising a plurality of pixel thin film transistors,

wherein the nonvolatile memory comprises a memory element,

wherein the memory element comprises a first thin film transistor comprising a floating gate and a second thin film transistor,

wherein gate electrodes of the plurality of pixel thin film transistors, the floating gate, and a gate electrode of the second thin film transistor comprise the same material, and

wherein a source electrode and a drain electrode of the memory element comprise

the same material as that of a gate electrode of the first thin film transistor.

5. An electronic device according to claim 1, wherein the floating gate, and a gate electrode of the second thin film transistor comprise the same material.

6. An electronic device according to claim 2, wherein the floating gate, and a gate electrode of the second thin film transistor comprise the same material.

7. An electronic device according to claim 1, wherein a source electrode and a drain electrode of the memory element comprise the same material as that of a gate electrode of the first thin film transistor.

8. An electronic device according to claim 3, wherein a source electrode and a drain electrode of the memory element comprise the same material as that of a gate electrode of the first thin film transistor.

9. An electronic device according to claim 1, wherein each of the first thin film transistor and the second thin film transistor comprises a semiconductor layer comprising a source region, a drain region, a low concentration impurity region, and a channel region.

10. An electronic device according to claim 2, wherein each of the first thin film transistor and the second thin film transistor comprises a semiconductor layer comprising a source region, a drain region, a low concentration impurity region, and a channel region.

11. An electronic device according to claim 3, wherein each of the pixel thin film transistors, the first thin film transistor, and the second thin film transistor comprises a semiconductor layer comprising a source region, a drain region, a low concentration impurity region, and a channel region.

12. An electronic device according to claim 4, wherein each of the pixel thin film transistors, the first thin film transistor, and the second thin film transistor comprises a semiconductor layer comprising a source region, a drain region, a low concentration impurity region, and a channel region.

13. An electronic device according to claim 1, wherein the first thin film transistor is a p-channel FAMOS type thin film transistor and the second thin film transistor is an n-channel switching thin film transistor.

14. An electronic device according to claim 2, wherein the first thin film transistor is a p-channel FAMOS type thin film transistor and the second thin film transistor is an n-channel switching thin film transistor.

15. An electronic device according to claim 3, wherein the first thin film transistor is a p-channel FAMOS type thin film transistor and the second thin film transistor is an n-channel switching thin film transistor.

16. An electronic device according to claim 4, wherein the first type thin film transistor is a p-channel FAMOS type thin film transistor and the second thin film transistor is an n-channel switching thin film transistor.

17. An electronic device according to claim 1, wherein the electronic device is one of the group consisting of a projection display system, a video camera, a still camcra, a head mount display, a car navigation system, a personal computer, a portable information terminal.

18. An electronic device according to claim 2, wherein the electronic device is one of the group consisting of a projection display system, a video camera, a still camera, a head mount display, a car navigation system, a personal computer, a portable information terminal.

19. An electronic device according to claim 3, wherein the electronic device is one of the group consisting of a projection display system, a video camera, a still camera, a head mount display, a car navigation system, a personal computer, a portable information terminal.

20. An electronic device according to claim 4, wherein the electronic device is one of the group consisting of a projection display system, a video camera, a still camera, a head mount display, a car navigation system, a personal computer, a portable information terminal.